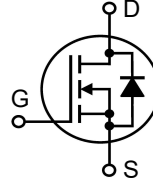


**X3-Class
HiPerFET™
Power MOSFET**

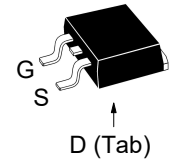
IXFA34N65X3

V_{DSS} = 650V
I_{D25} = 34A
R_{DS(on)} ≤ 100mΩ

N-Channel Enhancement Mode
Avalanche Rated



TO-263
(IXFA)



G = Gate D = Drain
S = Source Tab = Drain

Symbol	Test Conditions	Maximum Ratings	
V _{DSS}	T _J = 25°C to 150°C	650	V
V _{DGR}	T _J = 25°C to 150°C, R _{GS} = 1MΩ	650	V
V _{GSS}	Continuous	±20	V
V _{GSM}	Transient	±30	V
I _{D25}	T _C = 25°C	34	A
I _{DM}	T _C = 25°C, Pulse Width Limited by T _{JM}	48	A
I _A	T _C = 25°C	5	A
E _{AS}	T _C = 25°C	750	mJ
dv/dt	I _S ≤ I _{DM} , V _{DD} ≤ V _{DSS} , T _J ≤ 150°C	50	V/ns
P _D	T _C = 25°C	446	W
T _J		-55 ... +150	°C
T _{JM}		150	°C
T _{stg}		-55 ... +150	°C
T _{SOLD}	Plastic Body for 10s	260	°C
F _C	Mounting Force	10..65 / 2.2..14.6	N/lb
Weight		2.5	g

Features

- International Standard Package
- Low R_{DS(ON)} and Q_G
- Avalanche Rated
- Low Package Inductance

Advantages

- High Power Density
- Easy to Mount
- Space Savings

Applications

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- PFC Circuits
- AC and DC Motor Drives
- Robotics and Servo Controls

Symbol	Test Conditions (T _J = 25°C, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV _{DSS}	V _{GS} = 0V, I _D = 1mA	650		V
V _{GS(th)}	V _{DS} = V _{GS} , I _D = 2.5mA	3.2		5.2 V
I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±100 nA
I _{DSS}	V _{DS} = V _{DSS} , V _{GS} = 0V T _J = 125°C			25 μA 3 mA
R _{DS(on)}	V _{GS} = 10V, I _D = 0.5 • I _{D25} , Note 1			100 mΩ

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max
g_{fs}	$V_{DS} = 10\text{V}$, $I_D = 0.5 \cdot I_{D25}$, Note 1	13	22	S
R_{Gi}	Gate Input Resistance		1.7	Ω
C_{iss}	} $V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$		2025	pF
C_{oss}			2800	pF
C_{rss}			2.6	pF
Effective Output Capacitance				
$C_{o(er)}$	Energy related	} $V_{GS} = 0\text{V}$ $V_{DS} = 0.8 \cdot V_{DSS}$	100	pF
$C_{o(tr)}$	Time related		440	pF
$t_{d(on)}$	} Resistive Switching Times $V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$ $R_G = 10\Omega$ (External)		24	ns
t_r			10	ns
$t_{d(off)}$			47	ns
t_f			6	ns
$Q_{g(on)}$	} $V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$		29	nC
Q_{gs}			11	nC
Q_{gd}			10	nC
R_{thJC}				0.28 $^\circ\text{C/W}$

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max
I_S	$V_{GS} = 0\text{V}$			34 A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			136 A
V_{SD}	$I_F = I_S$, $V_{GS} = 0\text{V}$, Note 1			1.4 V
t_{rr}	} $I_F = 17\text{A}$, $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}$		150	ns
Q_{RM}			1.05	μC
I_{RM}			14.0	A

Note: 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

Littelfuse reserves the right to change limits, test conditions and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065B1	6,683,344	6,727,585	7,005,734B2	7,157,338B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123B1	6,534,343	6,710,405B2	6,759,692	7,063,975B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728B1	6,583,505	6,710,463	6,771,478B2	7,071,537	

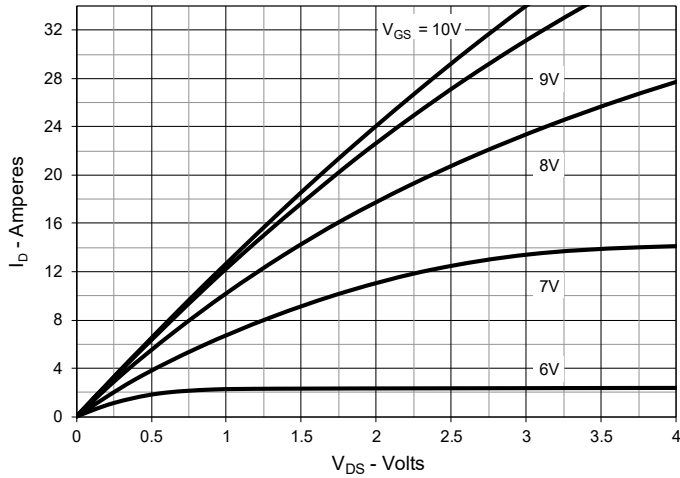
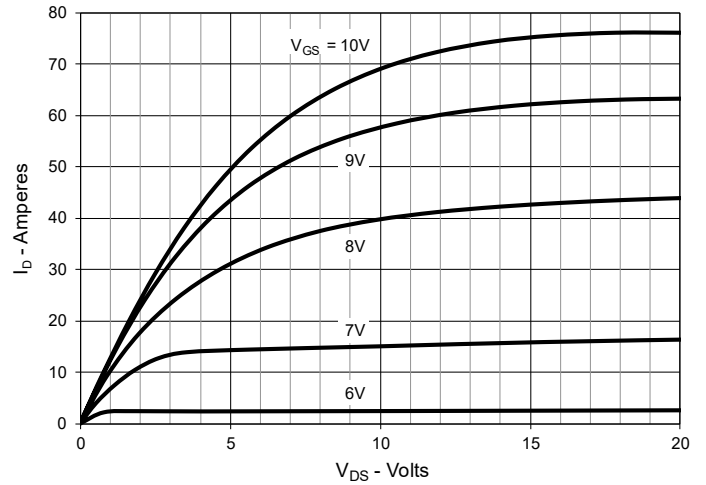
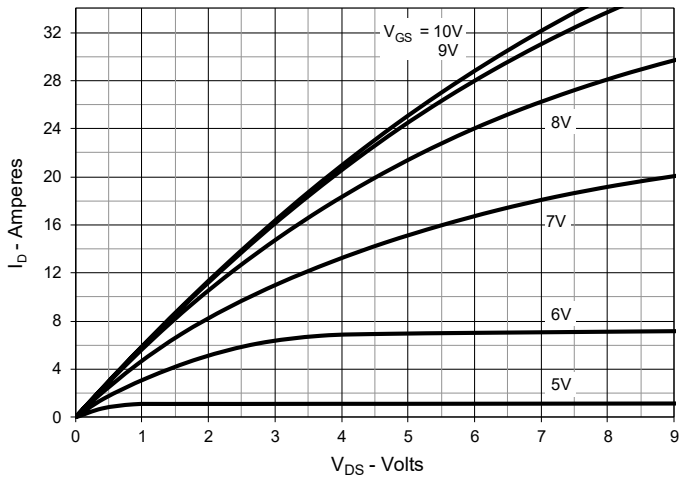
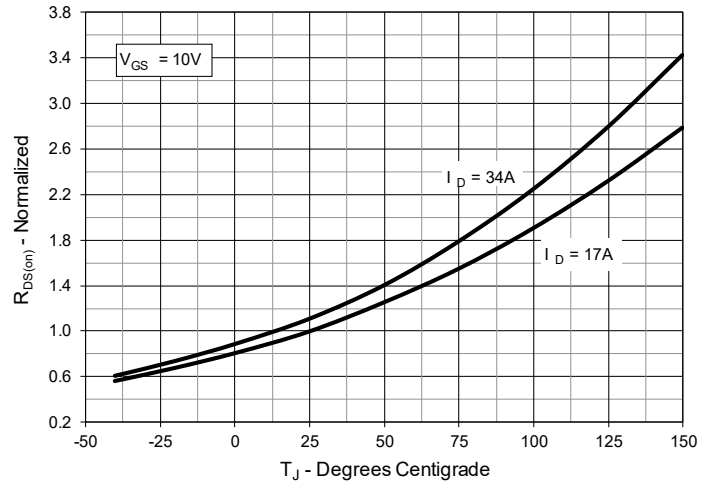
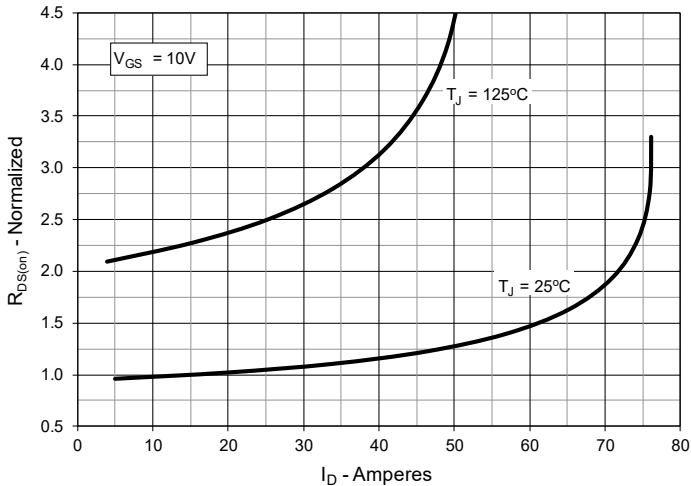
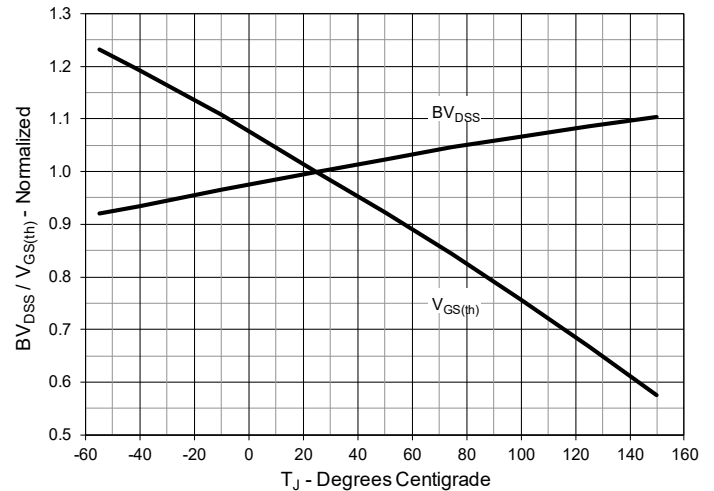
Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 17\text{A}$ Value vs. Junction Temperature

Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 17\text{A}$ Value vs. Drain Current

Fig. 6. Normalized Breakdown & Threshold Voltages vs. Junction Temperature


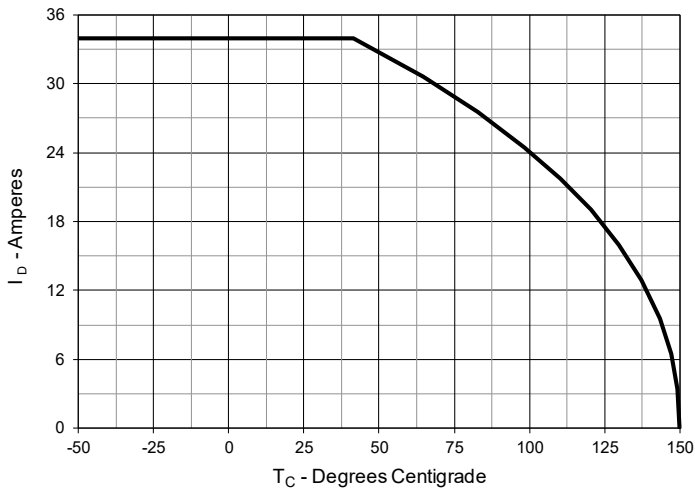
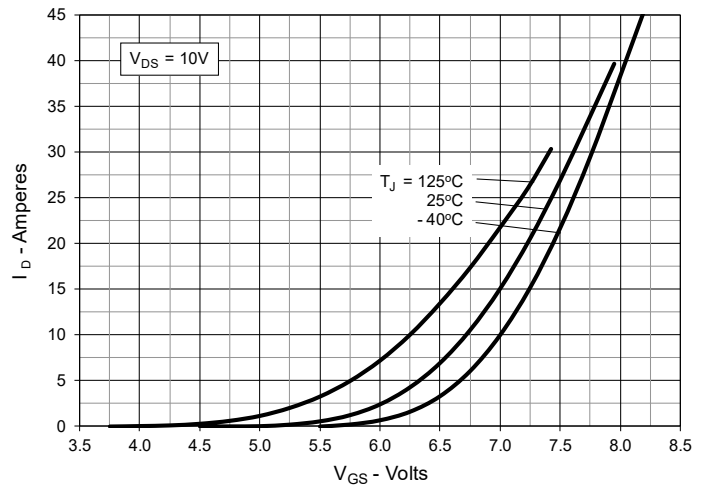
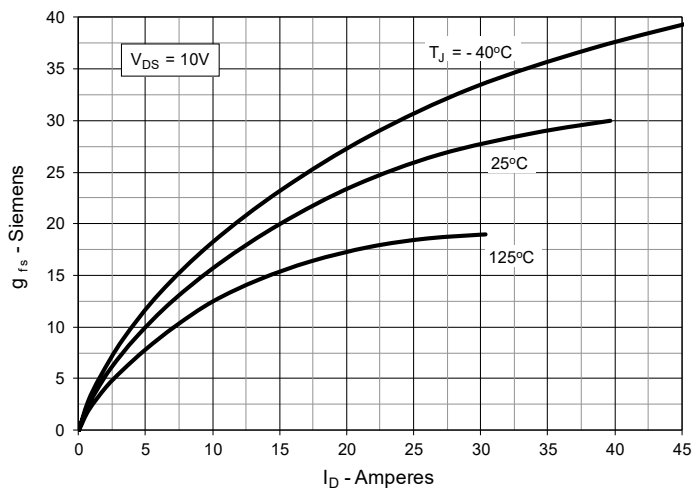
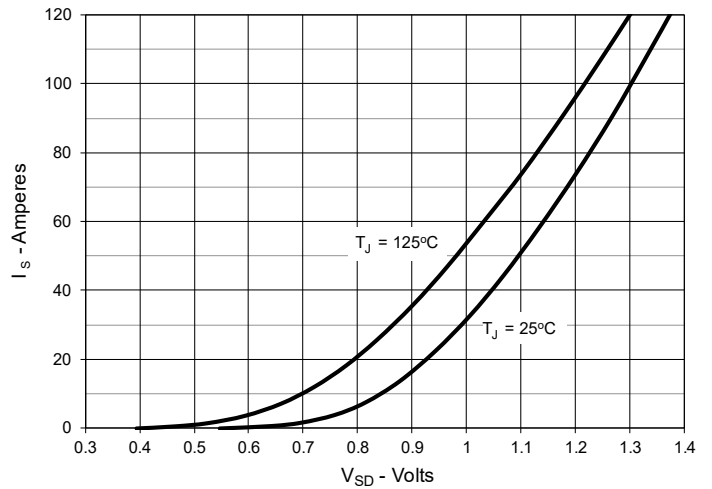
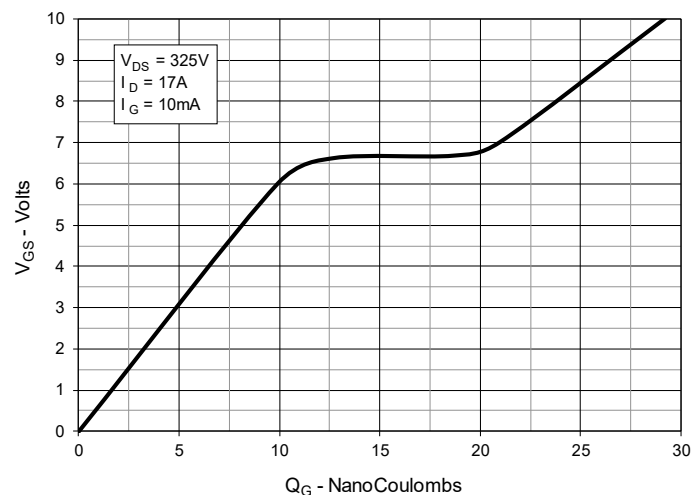
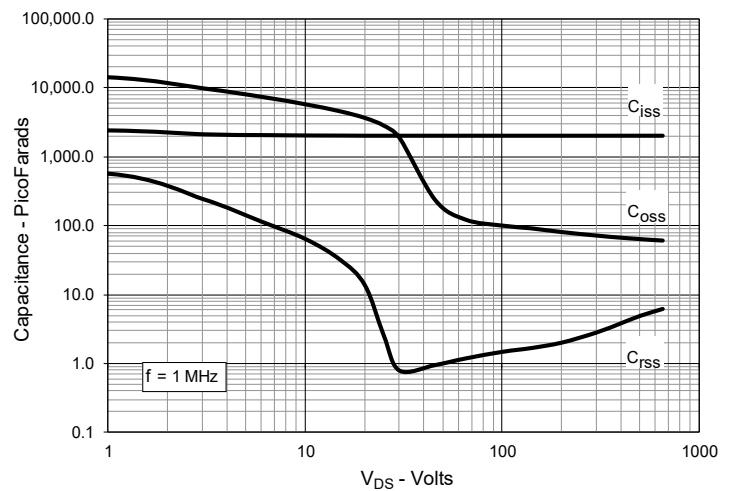
Fig. 7. Maximum Drain Current vs. Case Temperature

Fig. 8. Input Admittance

Fig. 9. Transconductance

Fig. 10. Forward Voltage Drop of Intrinsic Diode

Fig. 11. Gate Charge

Fig. 12. Capacitance


Fig. 13. Output Capacitance Stored Energy

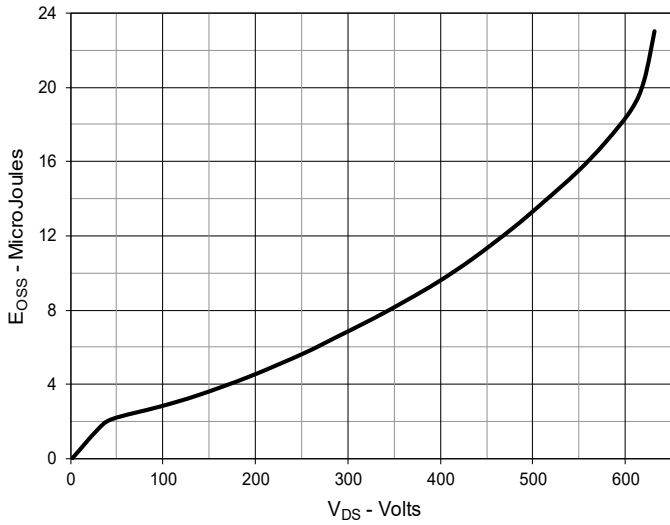


Fig. 14. Forward-Bias Safe Operating Area

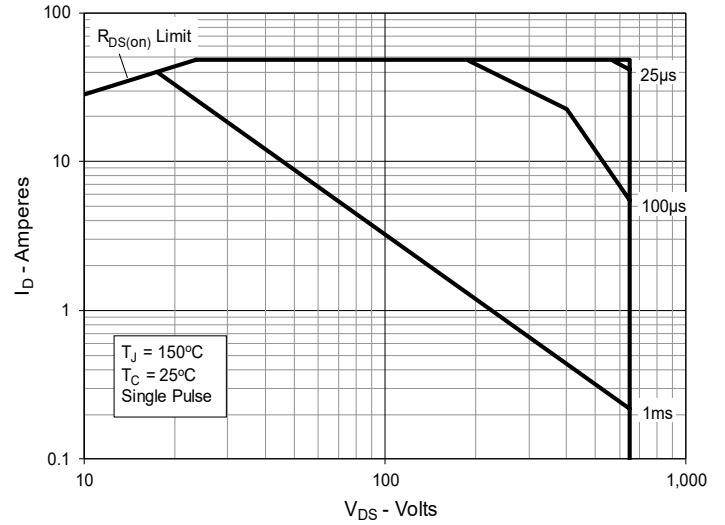
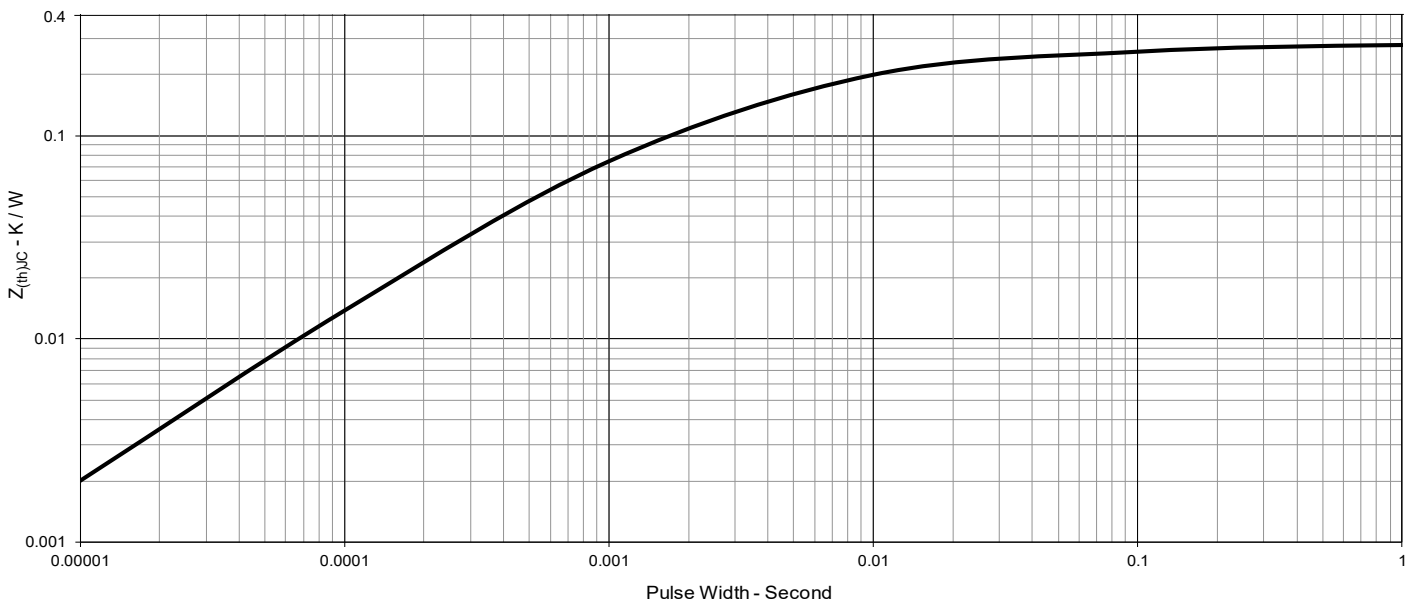
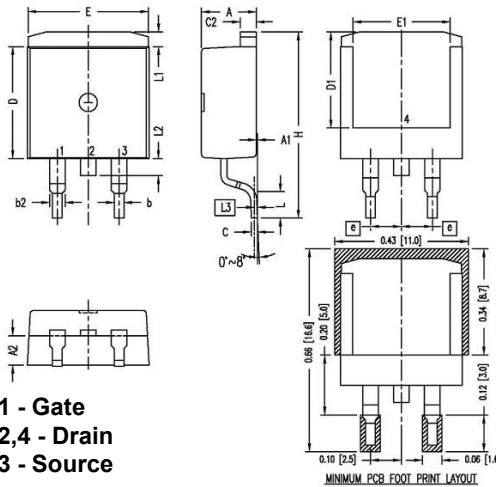


Fig. 15. Maximum Transient Thermal Impedance



TO-263 Outline


- 1 - Gate
- 2,4 - Drain
- 3 - Source

SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.170	.185	4.30	4.70
A1	.000	.008	0.00	0.20
A2	.091	.098	2.30	2.50
b	.028	.035	0.70	0.90
b2	.046	.060	1.18	1.52
C	.018	.024	0.45	0.60
C2	.049	.060	1.25	1.52
D	.340	.370	8.63	9.40
D1	.300	.327	7.62	8.30
E	.380	.410	9.65	10.41
E1	.270	.330	6.86	8.38
e	.100 BSC		2.54 BSC	
H	.580	.620	14.73	15.75
L	.075	.105	1.91	2.67
L1	.039	.060	1.00	1.52
L2	—	.070	—	1.77
L3	.010 BSC		0.254 BSC	